

[METHOD FOR DESCREENING NUMBER OF PARTICLES DURING ETCHING PROCESS]

Abstract of Disclosure

A method for decreasing a number of particles during an etching process of a material layer is described, in which a wafer is put on a susceptor in an etching chamber. A series of etching tests are conducted at first under the same conditions as in the etching process but with various susceptor heights, and the obtained data is analyzed to find an optimum height that results in a minimum deviation of etching depth. A normal etching process is then performed to the wafer with the height of the susceptor being adjusted to the optimum one to improve the uniformity of etching rate.

Figures